

NE3516S02

Data Sheet

R09DS0038EJ0100

Rev.1.00

Apr 16, 2012

N-Channel GaAs HJ-FET, X to Ku Band Low Noise and High-Gain

FEATURES

- Low noise figure and high associated gain
 $NF = 0.35 \text{ dB TYP.}, G_a = 14 \text{ dB TYP. @ } f = 12 \text{ GHz}, V_{DS} = 2 \text{ V}, I_D = 10 \text{ mA}$
 $NF = 0.35 \text{ dB TYP.}, G_a = 13.5 \text{ dB TYP. @ } f = 12 \text{ GHz}, V_{DS} = 2 \text{ V}, I_D = 6 \text{ mA (Reference Value)}$
- 4-pin Micro-X plastic (S02) package

APPLICATIONS

- X to Ku band DBS LNB
- Other Ku band communication system

ORDERING INFORMATION

Part Number	Order Number	Package	Quantity	Marking	Supplying Form
NE3516S02-T1C	NE3516S02-T1C-A	S02 package (Pb-Free)	2 kpcs/reel	P	<ul style="list-style-type: none"> 8 mm wide embossed taping Pin 4 (Gate) faces the perforation side of the tape
NE3516S02-T1D	NE3516S02-T1D-A		10 kpcs/reel		

Remark To order evaluation samples, please contact your nearby sales office.
 Part number for sample order: NE3516S02-A

ABSOLUTE MAXIMUM RATINGS ($T_A = +25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Drain to Source Voltage	V_{DS}	4.0	V
Gate to Source Voltage	V_{GS}	-3.0	V
Drain Current	I_D	I_{DSS}	mA
Gate Current	I_G	100	μA
Total Power Dissipation ^{Note}	P_{tot}	165	mW
Channel Temperature	T_{ch}	+125	$^\circ\text{C}$
Storage Temperature	T_{stg}	-65 to +125	$^\circ\text{C}$

Note: Mounted on $1.08 \text{ cm}^2 \times 1.0 \text{ mm (t)}$ glass epoxy PWB

RECOMMENDED OPERATING RANGE ($T_A = +25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Drain to Source Voltage	V_{DS}	+1	+2	+3	V
Drain Current	I_D	5	10	15	mA
Input Power	P_{in}	-	-	0	dBm

CAUTION

Observe precautions when handling because these devices are sensitive to electrostatic discharge.

NE3516S02**ELECTRICAL CHARACTERISTICS ($T_A = +25^\circ\text{C}$, unless otherwise specified)**

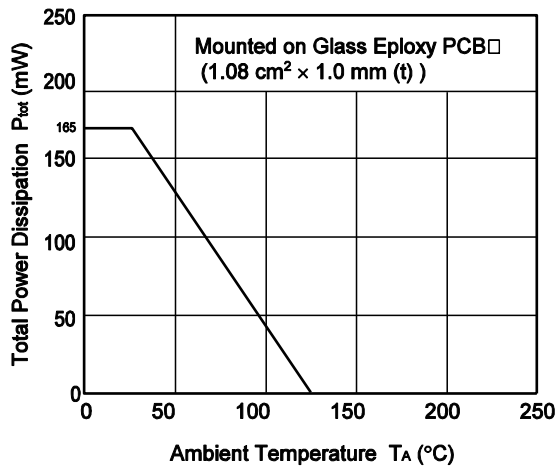
Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Gate to Source Leak Current	I_{GSO}	$V_{GS} = -3.0\text{ V}$	–	0.5	10	μA
Saturated Drain Current	I_{DSS}	$V_{DS} = 2\text{ V}, V_{GS} = 0\text{ V}$	15	30	60	mA
Gate to Source Cut-off Voltage	$V_{GS(off)}$	$V_{DS} = 2\text{ V}, I_D = 100\text{ }\mu\text{A}$	–0.2	–0.5	–1.3	V
Transconductance	gm	$V_{DS} = 2\text{ V}, I_D = 10\text{ mA}$	55	65	–	mS
Noise Figure	NF	$V_{DS} = 2\text{ V}, I_D = 10\text{ mA}, f = 12\text{ GHz}$	–	0.35	0.50	dB
Associated Gain	G_a		13	14	–	dB

**STANDARD CHARACTERISTICS FOR REFERENCE
($T_A = +25^\circ\text{C}$, unless otherwise specified)**

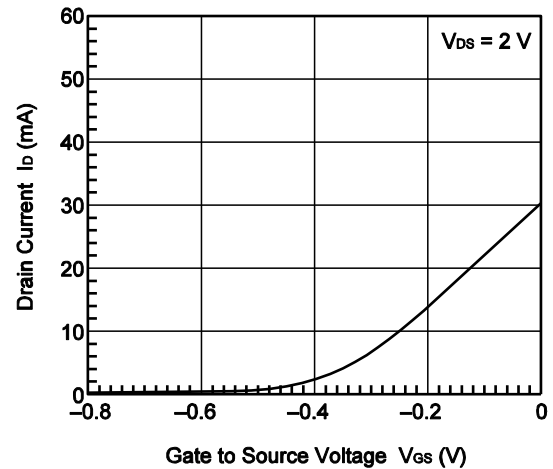
Parameter	Symbol	Test Conditions	Reference Value	Unit
Noise Figure	NF	$V_{DS} = 2\text{ V}, I_D = 6\text{ mA}, f = 12\text{ GHz}$	0.35	dB
Associated Gain	G_a		13.5	dB

TYPICAL CHARACTERISTICS ($T_A = +25^\circ\text{C}$, unless otherwise specified)

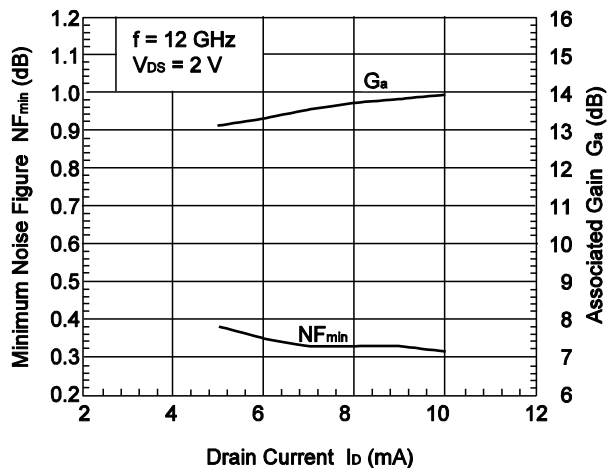
**TOTAL POWER DISSIPATION
vs. AMBIENT TEMPERATURE**



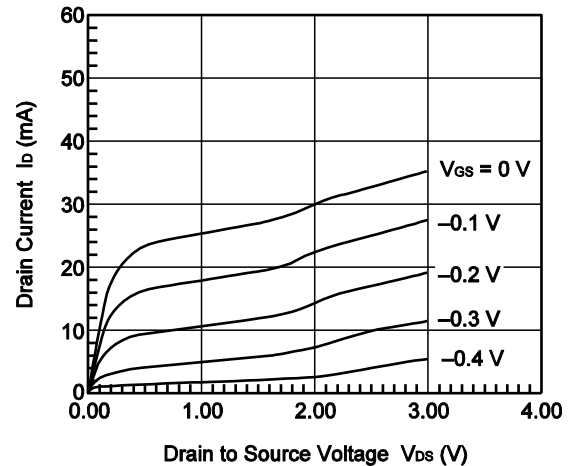
**DRAIN CURRENT vs.
GATE TO SOURCE VOLTAGE**



**MINIMUM NOISE FIGURE,
ASSOCIATED GAIN vs. DRAIN CURRENT**



**DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE**

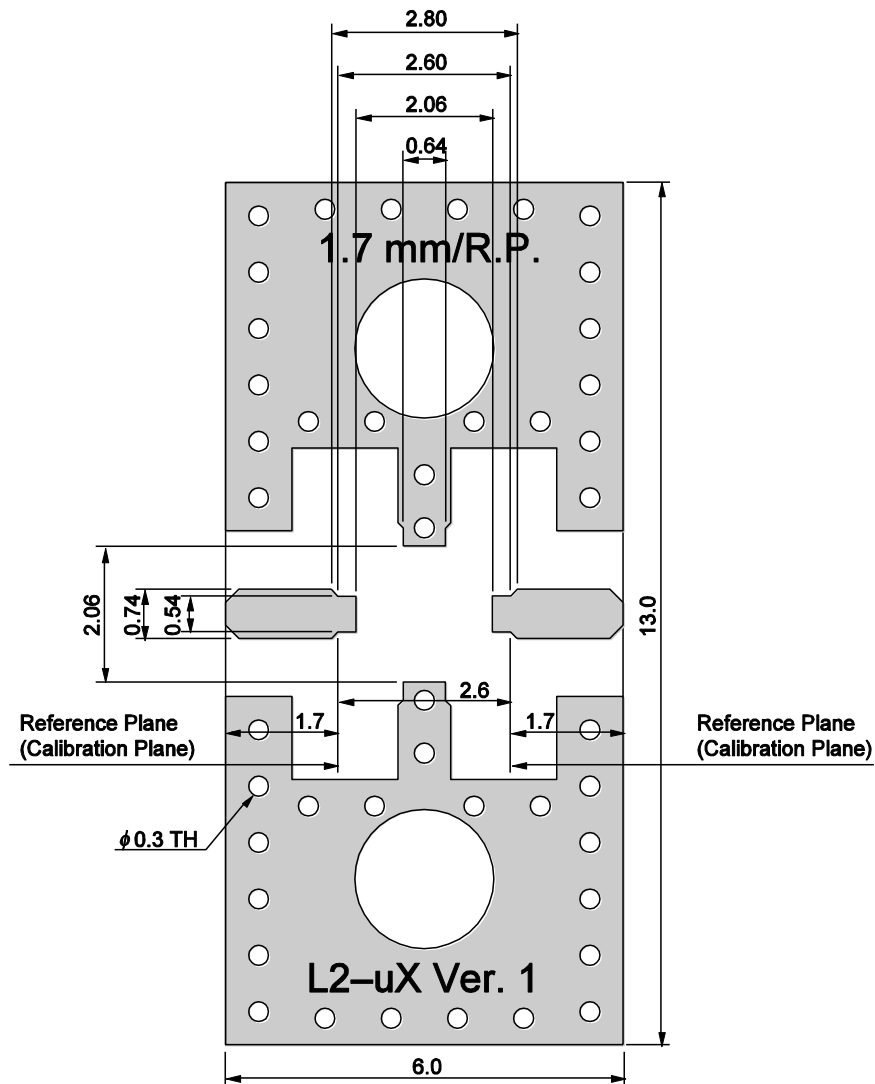


Remark The graph indicates nominal characteristics.

S-PARAMETERS

- S-parameters and noise parameters are provided on our web site in a form (S2P) that enables direct import to microwave circuit simulators without keyboard inputs.
- [Click here to download S-parameters.](#)
- [\[Products\]](#) → [\[RF Devices\]](#) → [\[Device Parameters\]](#)
- URL <http://www.renesas.com/products/microwave/download/parameter/>

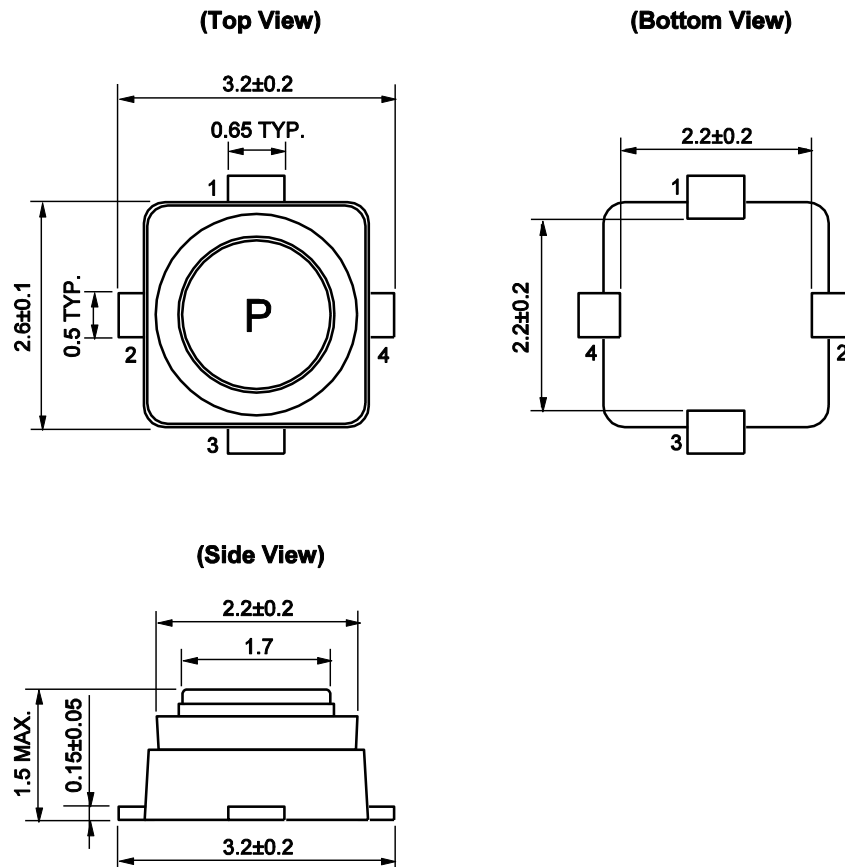
RF MEASURING LAYOUT PATTERN (REFERENCE ONLY) (UNIT: mm)



RT/duroid 5880/ROGERS
 $t = 0.254$ mm
 $\epsilon_r = 2.20$
 $\tan \delta = 0.0009 @ 10$ GHz

PACKAGE DIMENSIONS

S02 (UNIT: mm)



PIN CONNECTIONS

1. Source
2. Drain
3. Source
4. Gate

RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions	Condition Symbol
Infrared Reflow	Peak temperature (package surface temperature) : 260°C or below Time at peak temperature : 10 seconds or less Time at temperature of 220°C or higher : 60 seconds or less Preheating time at 120 to 180°C : 120±30 seconds Maximum number of reflow processes : 3 times Maximum chlorine content of rosin flux (% mass) : 0.2% (Wt.) or below	IR260
Partial Heating	Peak temperature (terminal temperature) : 350°C or below Soldering time (per side of device) : 3 seconds or less Maximum chlorine content of rosin flux (% mass) : 0.2% (Wt.) or below	HS350

CAUTION

Do not use different soldering methods together (except for partial heating).

Caution

GaAs Products

This product uses gallium arsenide (GaAs).

GaAs vapor and powder are hazardous to human health if inhaled or ingested, so please observe the following points.

- Follow related laws and ordinances when disposing of the product. If there are no applicable laws and/or ordinances, dispose of the product as recommended below.
 1. Commission a disposal company able to (with a license to) collect, transport and dispose of materials that contain arsenic and other such industrial waste materials.
 2. Exclude the product from general industrial waste and household garbage, and ensure that the product is controlled (as industrial waste subject to special control) up until final disposal.
- Do not burn, destroy, cut, crush, or chemically dissolve the product.
- Do not lick the product or in any way allow it to enter the mouth.

Revision History	NE3516S02 Data Sheet
-------------------------	-----------------------------

Rev.	Date	Description	
		Page	Summary
1.00	Apr 16, 2012	–	First edition issued